

Fig. 1

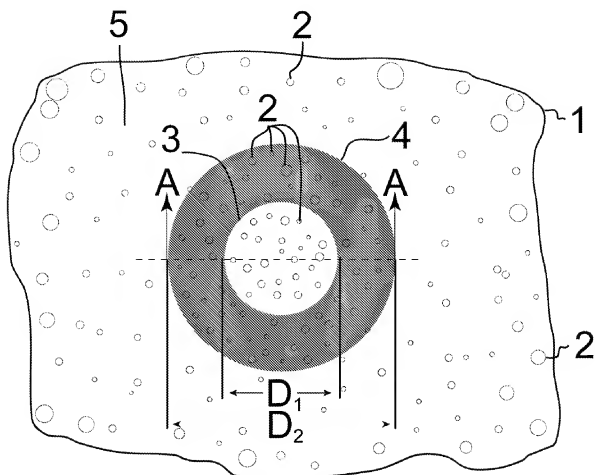


Fig. 2

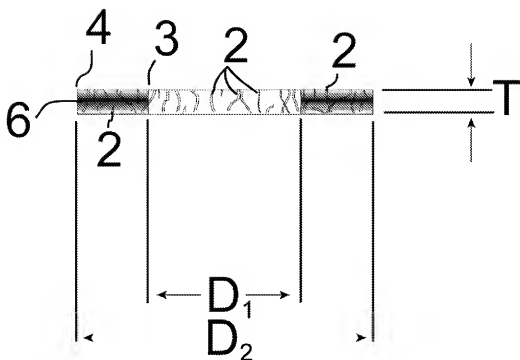


Fig. 3

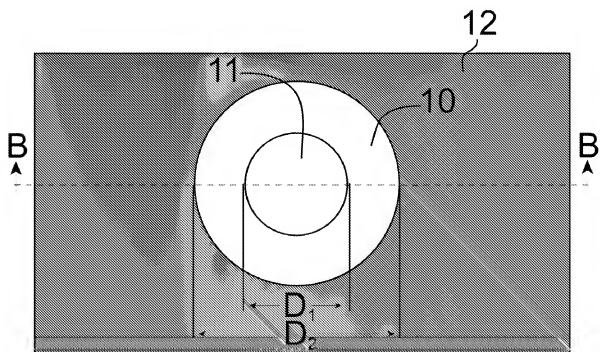


Fig. 4

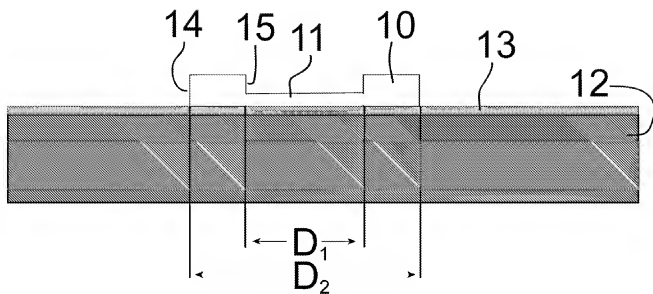


Fig.5

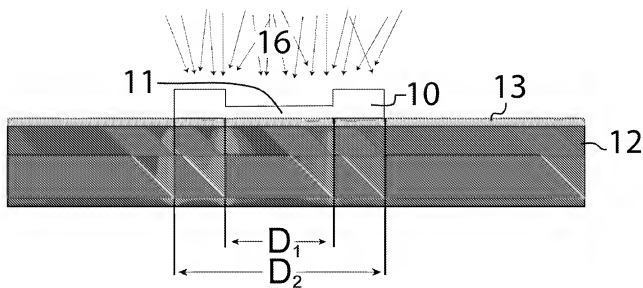


Fig. 6

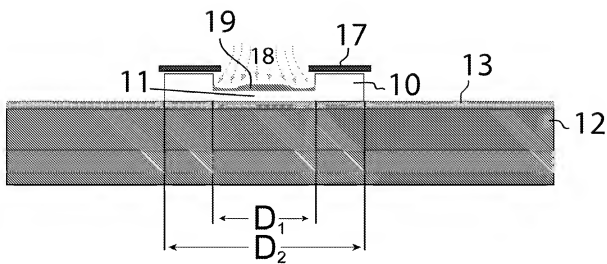
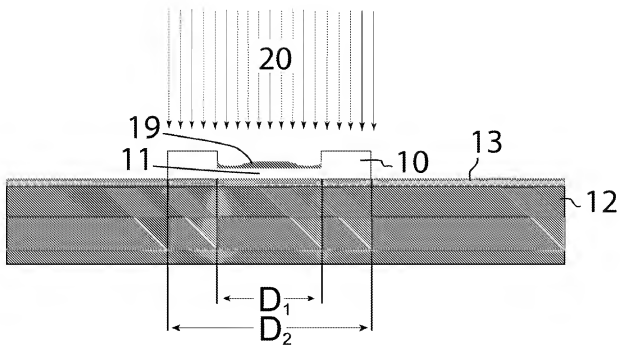


Fig. 7



A cross-sectional view of a semiconductor device. A substrate 12 is shown with a trench 10. The trench 10 has a bottom surface 11 and side surfaces 21. A layer 20 is deposited on the top surface of the substrate 12. The layer 20 has a top surface 22 and a bottom surface 24. The bottom surface 24 is located within the trench 10. A layer 23 is deposited on the top surface of the layer 20. The layer 23 has a top surface 24 and a bottom surface 22. The bottom surface 22 is located within the trench 10. The width of the trench 10 is indicated by D_1 and D_2 .

Fig. 10

